



# DCP68/-25

#### NPN SURFACE MOUNT TRANSISTOR

### **Features**

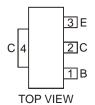
- **Epitaxial Planar Die Construction**
- Complementary PNP Type Available (DCP69)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

### **Mechanical Data**

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.115 grams









Schematic and Pin Configuration

#### Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Collector-Base Voltage	$V_{CBO}$	25	V
Collector-Emitter Voltage	V <sub>CEO</sub>	20	V
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	V
Collector Current	lc	1.0	А

### Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation @ T <sub>A</sub> = 25°C (Note 3)	$P_D$	1	W
Thermal Resistance, Junction to Ambient Air @ T <sub>A</sub> = 25°C (Note 3)	$R_{ hetaJA}$	125	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

# **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characte	ristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)							
Collector-Emitter Breakdown Voltage		V <sub>(BR)CES</sub>	25	_	_	V	$I_C = 100 \mu A, I_E = 0$
		$V_{(BR)CEO}$	20	_	_	V	$I_C = 1.0 \text{mA}, I_B = 0$
Collector-Base Breakdown Voltage		V <sub>(BR)CBO</sub>	25	_	_	V	$I_C = 10 \mu A, I_E = 0$
Emitter-Base Breakdown Voltage		V <sub>(BR)EBO</sub>	5.0	_	_	V	$I_E = 10\mu A, I_C = 0$
Collector-Base Cutoff Current		I <sub>CBO</sub>	_	_	100	nA	$V_{CB} = 25V, I_{E} = 0$
Emitter-Base Cutoff Current		I <sub>EBO</sub>	_	_	10	μΑ	$V_{EB} = 5.0V, I_{C} = 0$
ON CHARACTERISTICS (Note 4)							
	DCP68, DCP68-25	h <sub>FE</sub>	50	_	_		$V_{CE} = 10V, I_{C} = 5.0mA$
DC Current Gain	DCI 00, DCI 00-23		60	_	_		$V_{CE} = 1.0V, I_{C} = 1.0A$
DC Current Gain	DCP68		85	_	375		$V_{CE} = 1.0V, I_{C} = 500mA$
	DCP68-25		160	_	375		$V_{CE} = 1.0V, I_{C} = 500mA$
Collector-Emitter Saturation Voltage		V <sub>CE(SAT)</sub>	_	_	0.5	V	$I_C = 1.0A$ , $I_B = 100mA$
Base-Emitter Turn-On Voltage		V <sub>BE (ON)</sub>	_	_	1.0	V	$V_{CE} = 1.0V, I_{C} = 1.0A$
SMALL SIGNAL CHARACTERISTICS							
Current Gain-Bandwidth Product		f <sub>T</sub>	_	330	_	MHz	$I_C = 100$ mA, $V_{CE} = 5.0$ V $f = 100$ MHz

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 4. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.



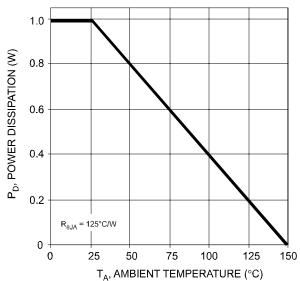
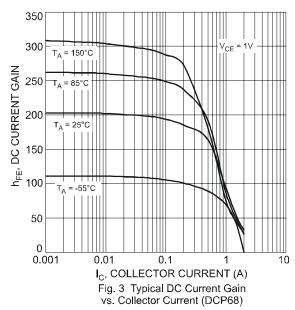
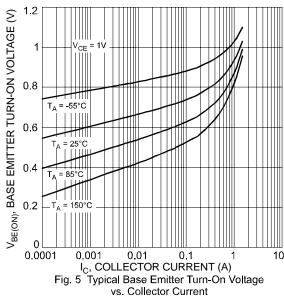
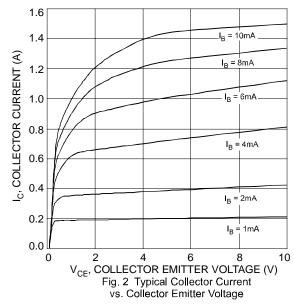


Fig. 1 Power Dissipation vs. Ambient Temperature







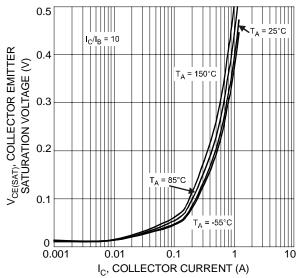


Fig. 4 Typical Collector Emitter Saturation Voltage vs. Collector Current

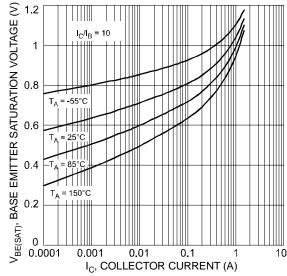
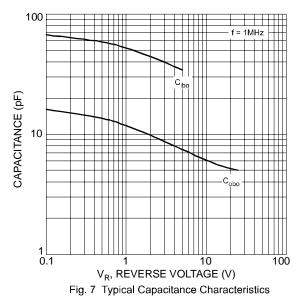
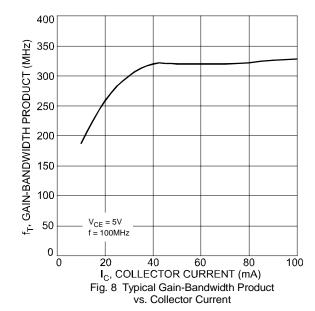


Fig. 6 Typical Base Emitter Saturation Voltage vs. Collector Current





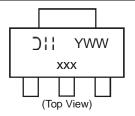


# **Ordering Information**

Device	Packaging	Shipping
DCP68-13	SOT-223	2500/Tape & Reel
DCP68-25-13	SOT-223	2500/Tape & Reel

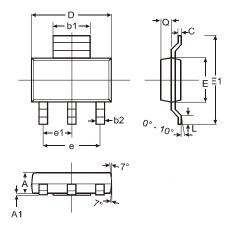
5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**



xxx = Product Type Marking Code: N12 = DCP68 N12-25 = DCP68-25 YWW = Date Code Marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

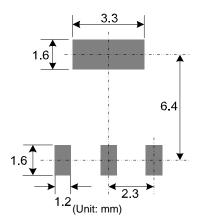
# **Package Outline Dimensions**



SOT-223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е			4.60		
e1			2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					



# **Suggested Pad Layout:**



#### IMPORTANT NOTICE

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. Diodes Incorporated does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others. The user of products in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on our website, harmless against all damages.

#### LIFE SUPPORT

Diodes Incorporated products are not authorized for use as critical components in life support devices or systems without the expressed written approval of the President of Diodes Incorporated.

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by Diodes Incorporated manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H BC546/116 BC557/116 BSW67A NTE187A NTE195A NTE2302 NTE2330 NTE63 C4460 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA2126-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMMTA92QTA 2N2369ADCSM 2SC2412KT146S 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E US6T6TR 732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H 873787E UMX21NTR EMT2T2R MCH6102-TL-E FP204-TL-E NJL0302DG 2N3583 2SA1434-TB-E 2SC3143-4-TB-E 2SD1621S-TD-E 30A02MH-TL-E NSV40301MZ4T1G NTE13 NTE15 NTE16001 NTE16006 NTE26 NTE320